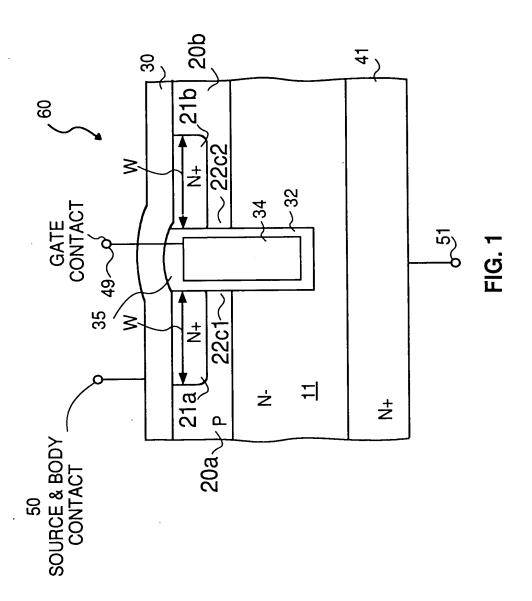
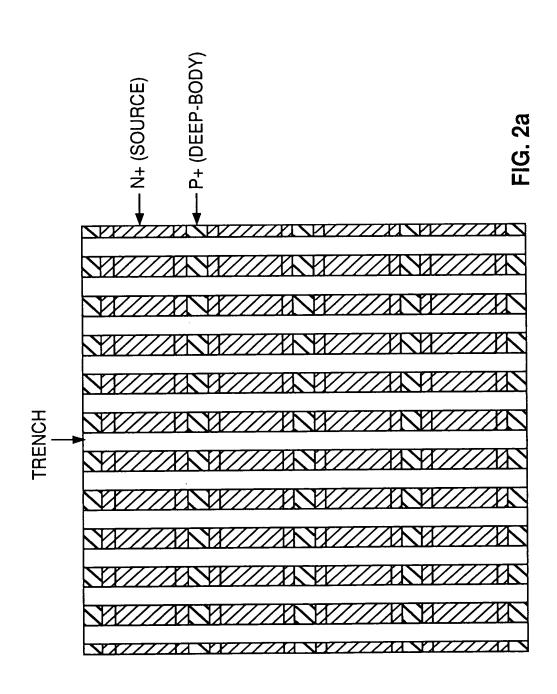




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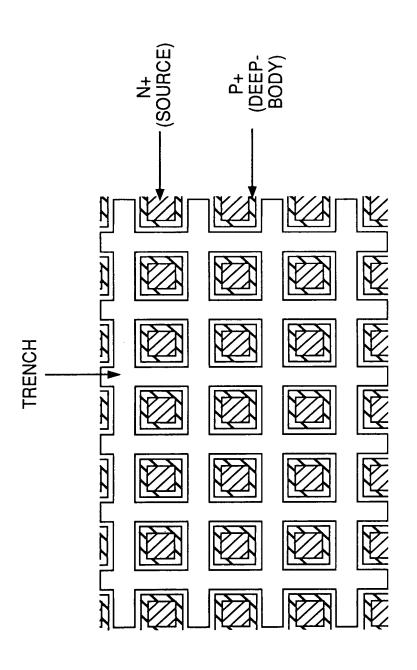


FIG. 2b

VERT/DIV 10 mA CURSOR 0.1 mA HORIZ/DIV 5 V CURSOR -0.45 V PER STEP 500 mV OFFSET 0 mV 8 or gm/DIV 20mS 20mS AUX SUPPLY

FIG. 3a

3.5

A2.4/QD5.3



VERT/DIV 10 mA CURSOR 0.1 mA HORIZ/DIV 5 V CURSOR -0.15 V PER STEP 500 mV OFFSET 0 mV 20mS 20mS 20mS AUX SUPPLY

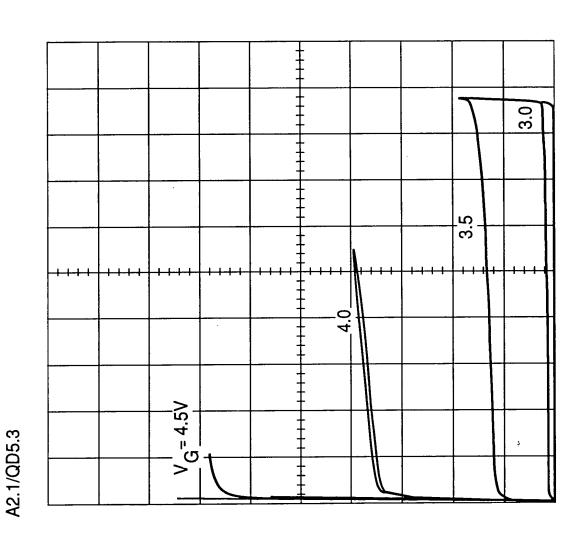
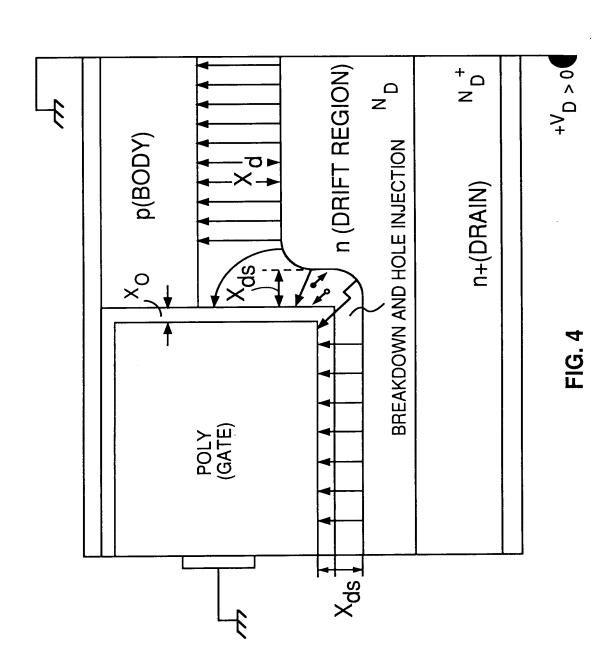
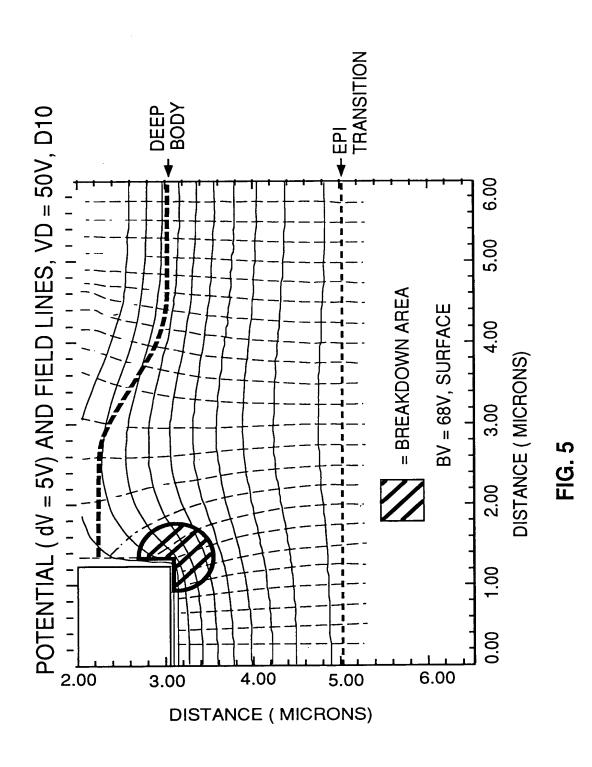


FIG. 3b

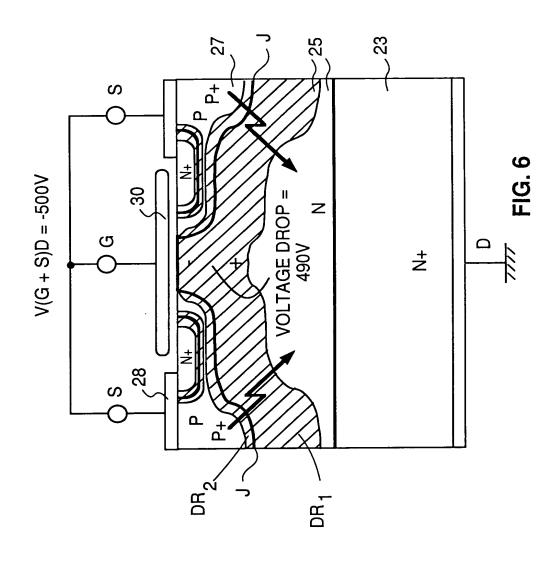




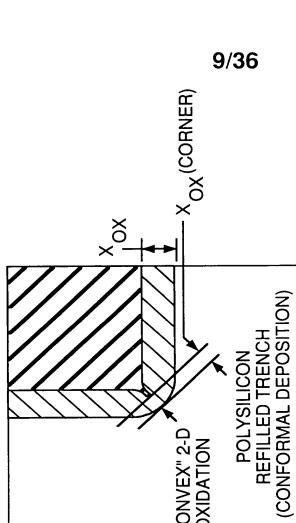








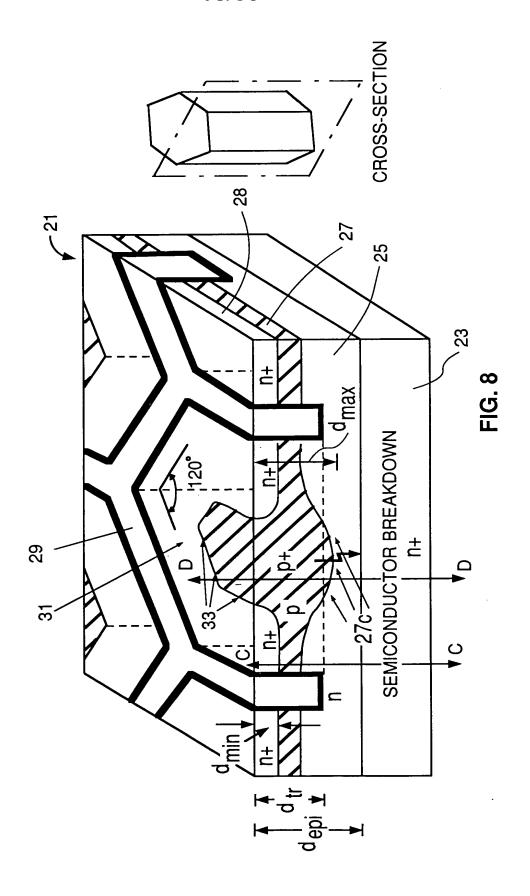
2-D OXIDATION SQUARE-CELL DESIGN



"CONVEX" 2-D OXIDATION

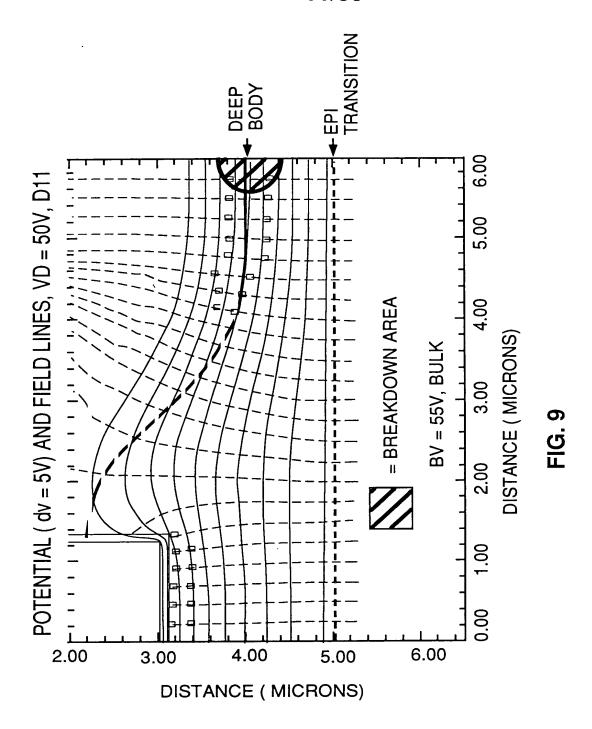
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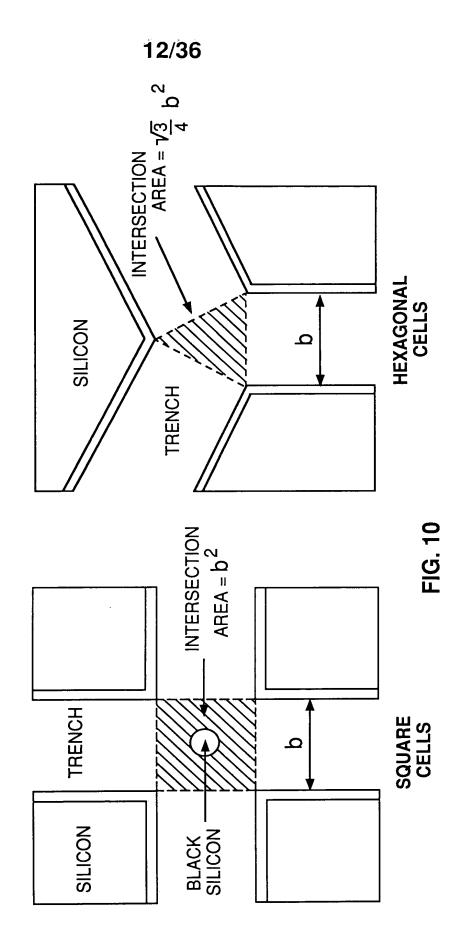




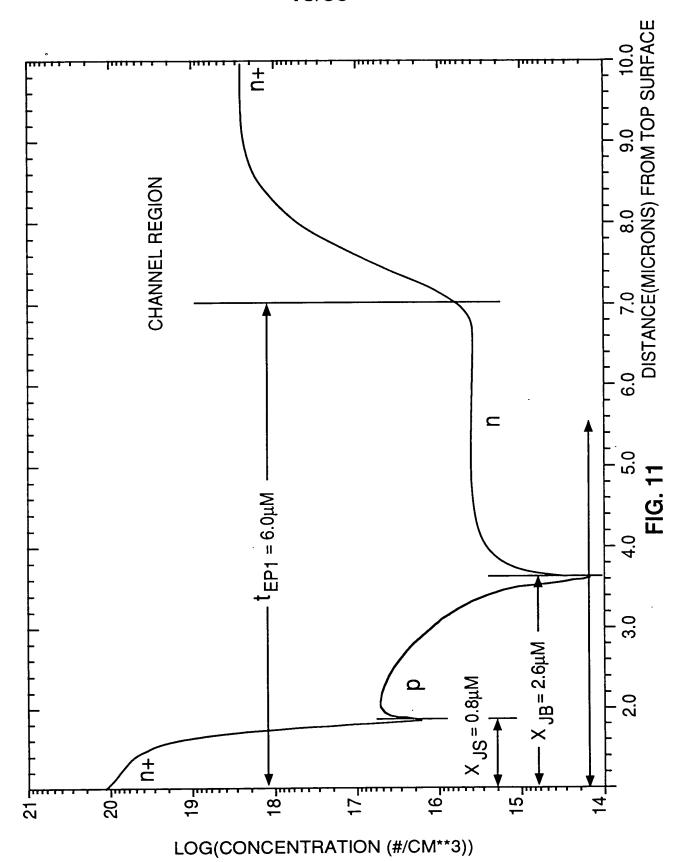


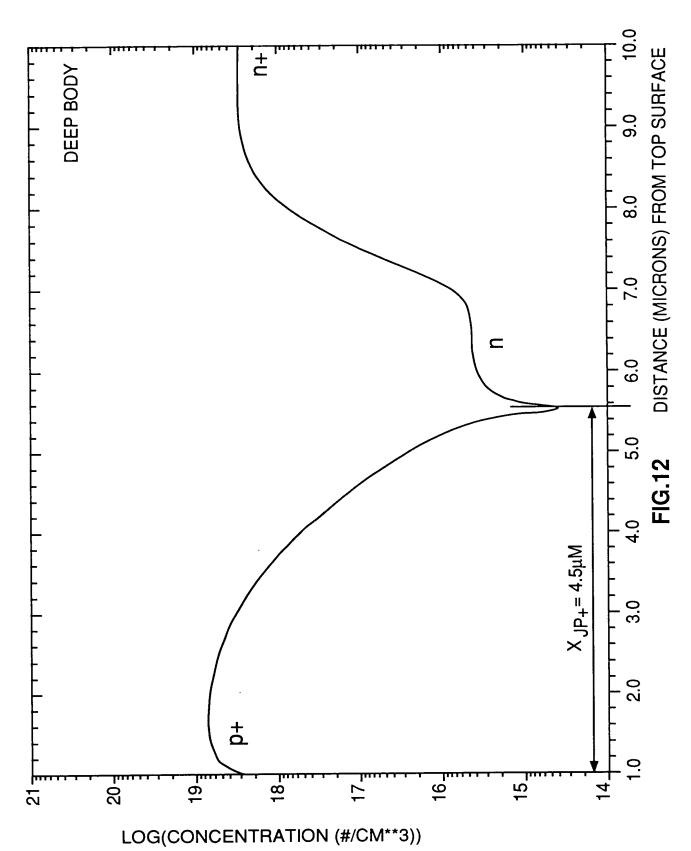




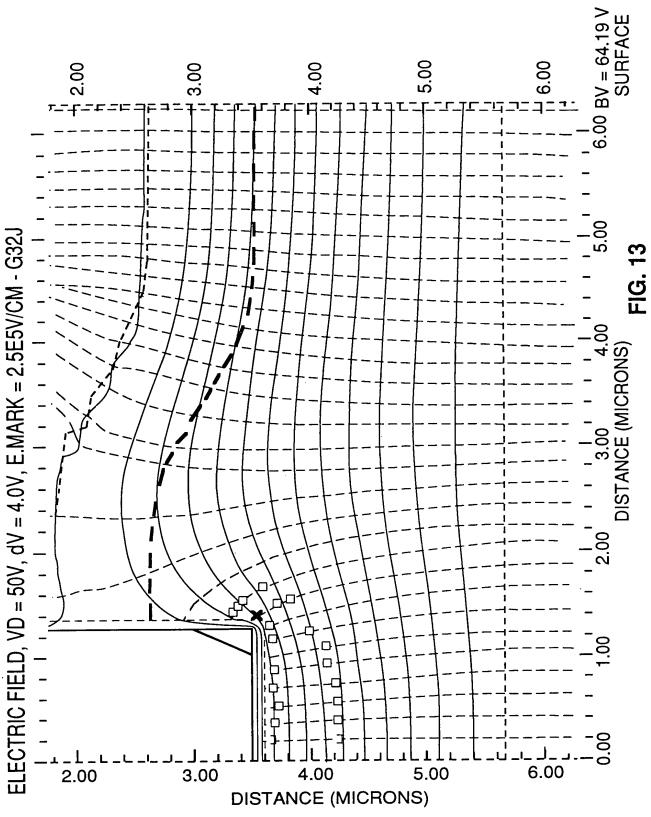




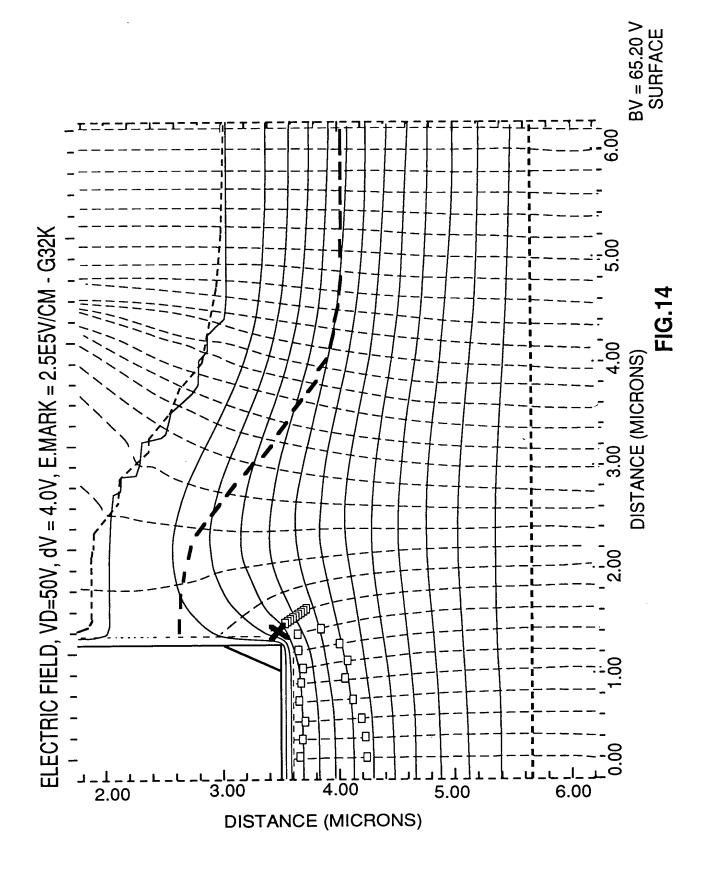


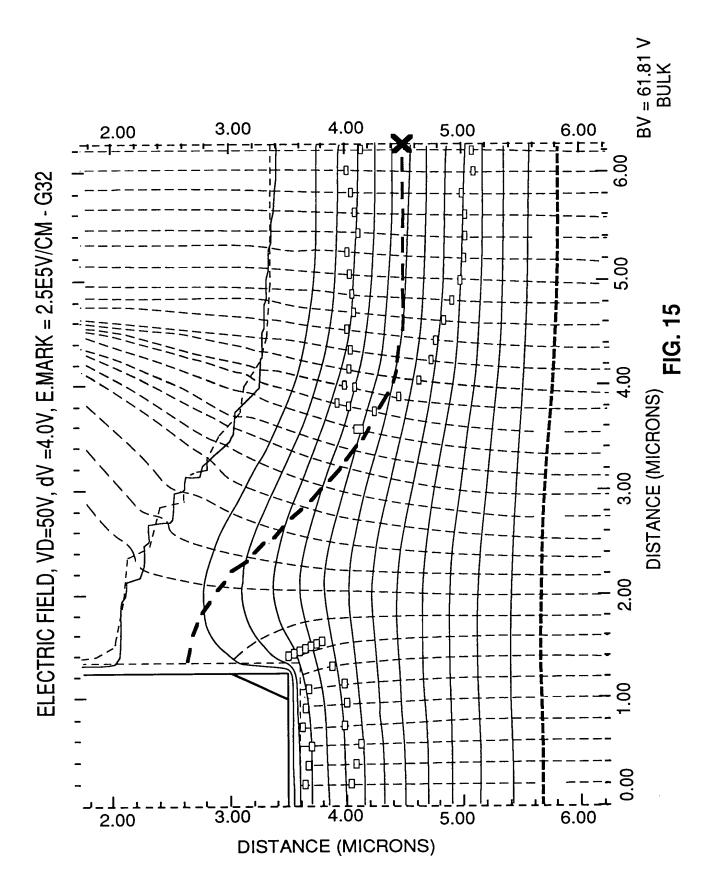




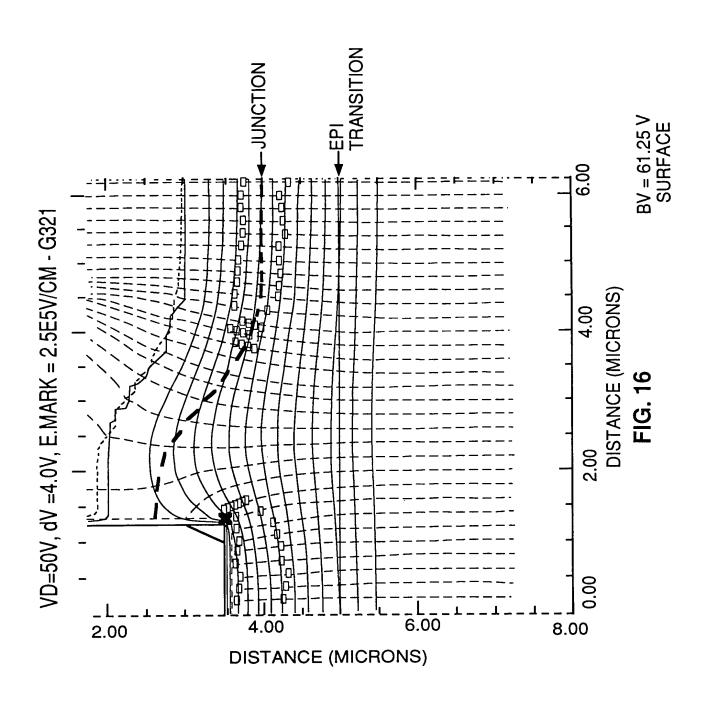


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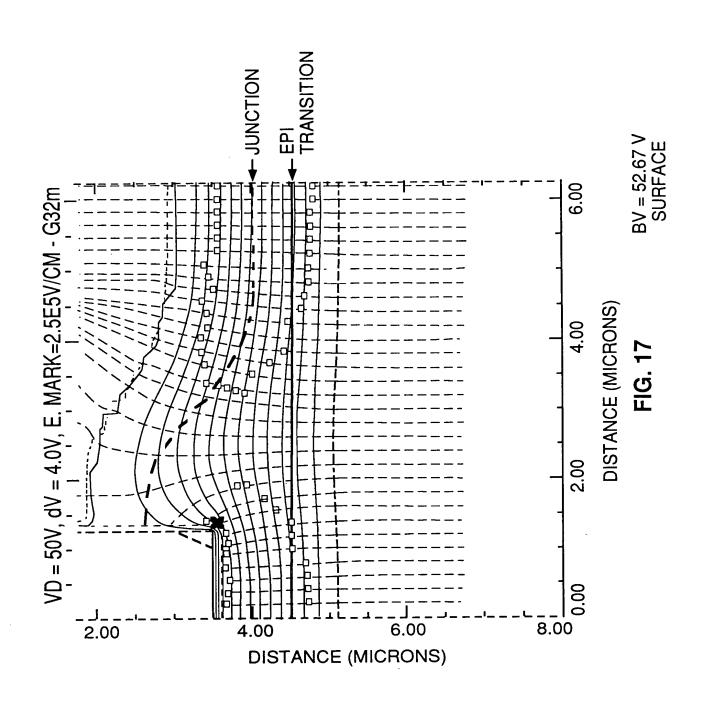






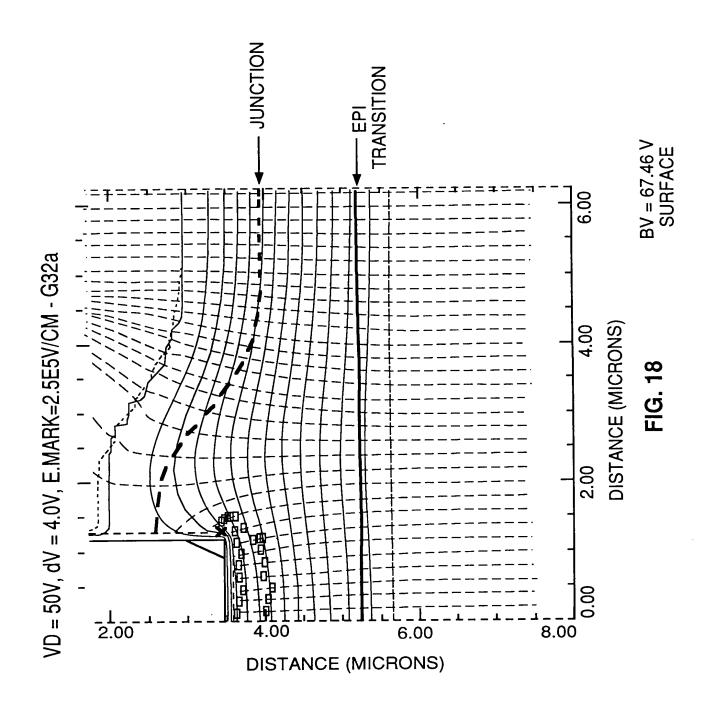


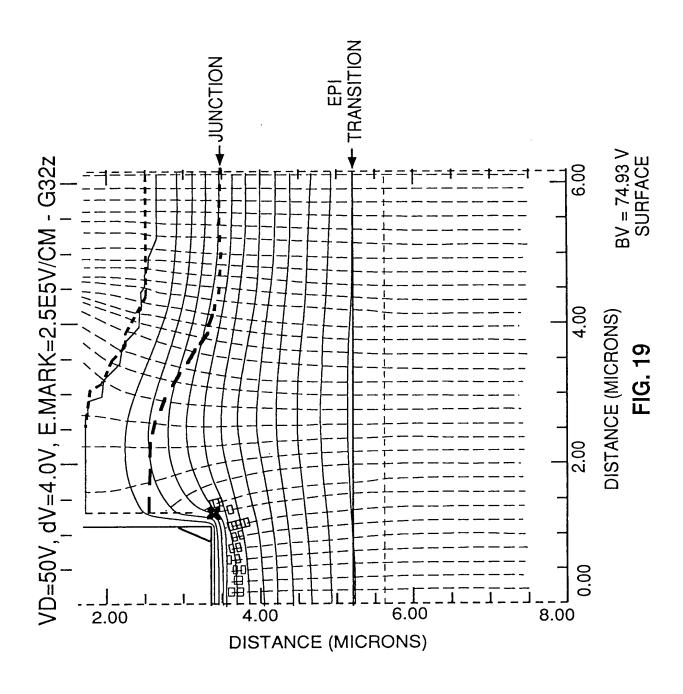


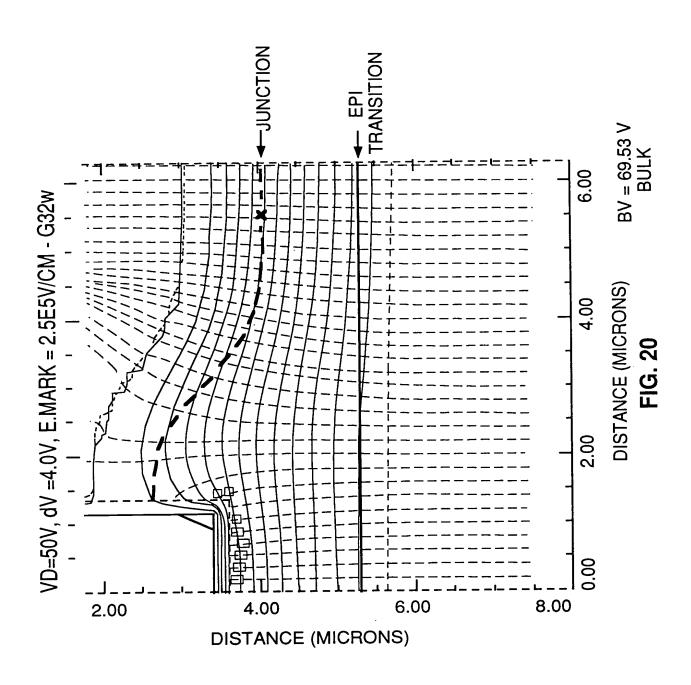




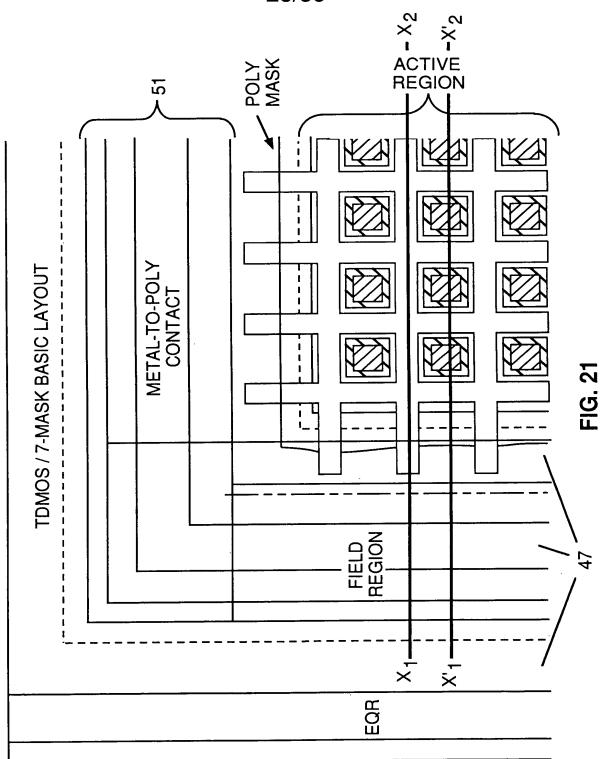
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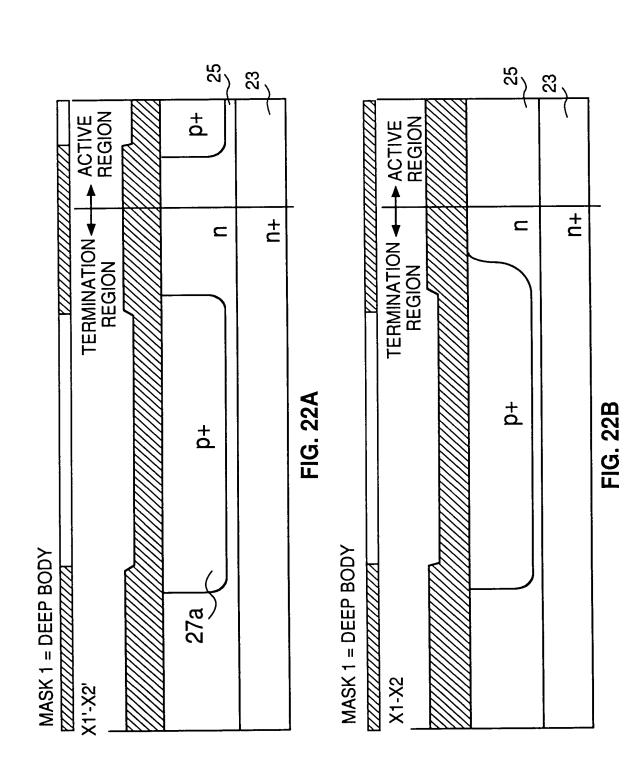




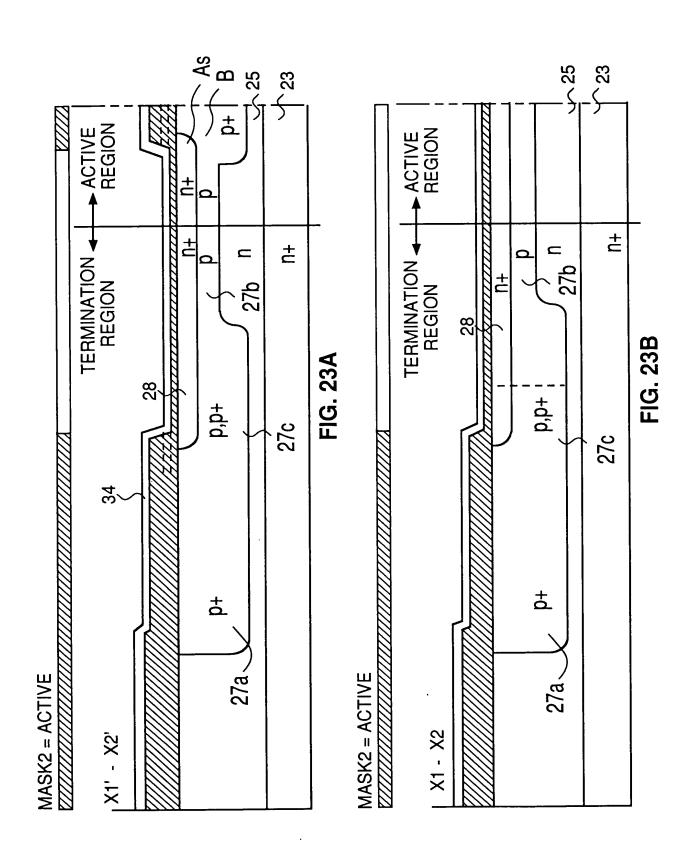














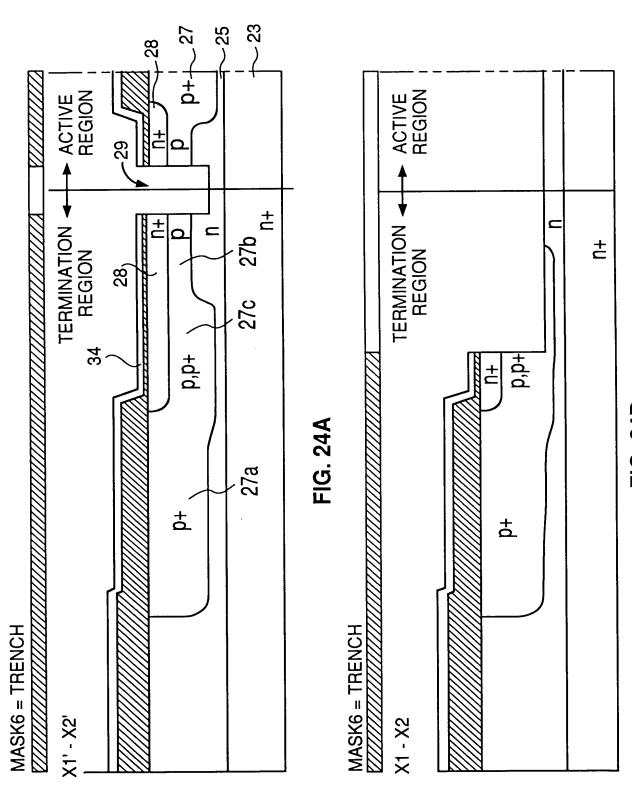
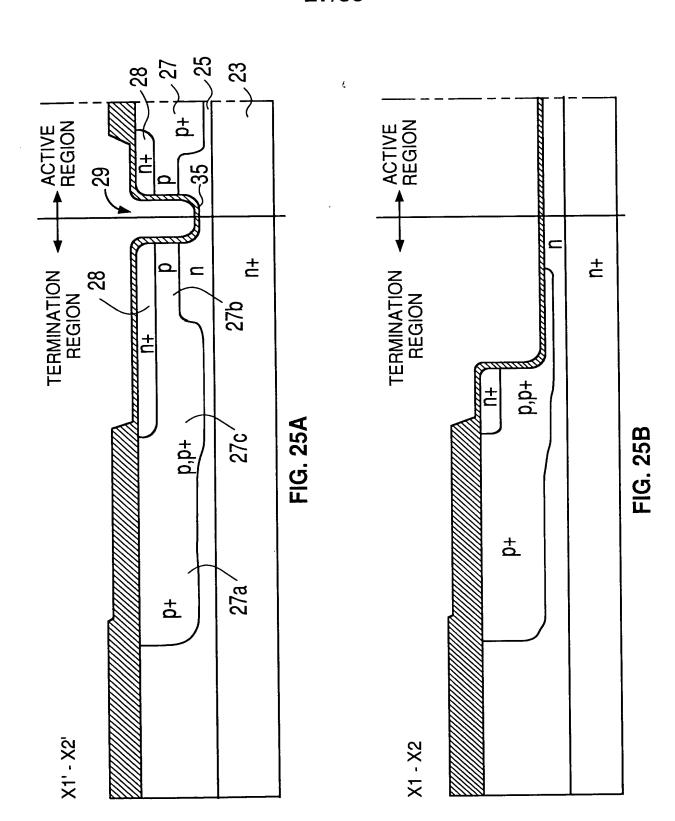


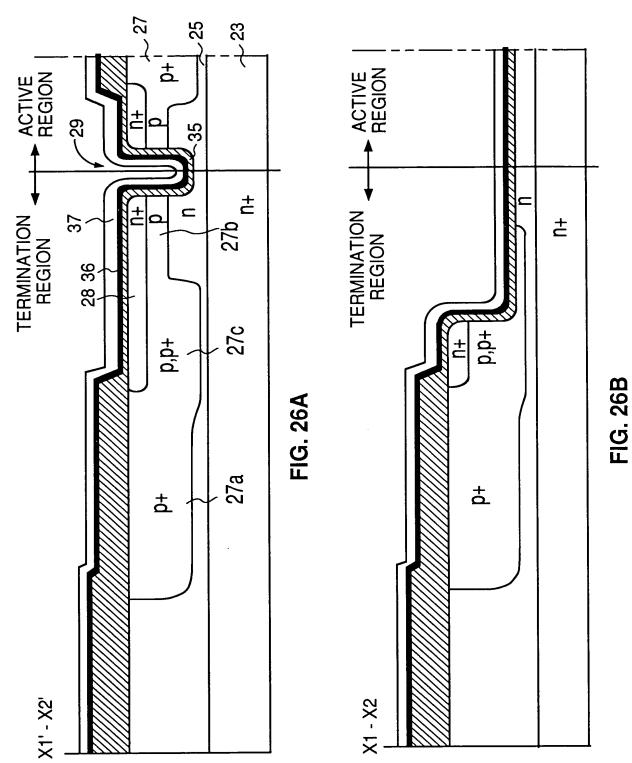
FIG. 24B



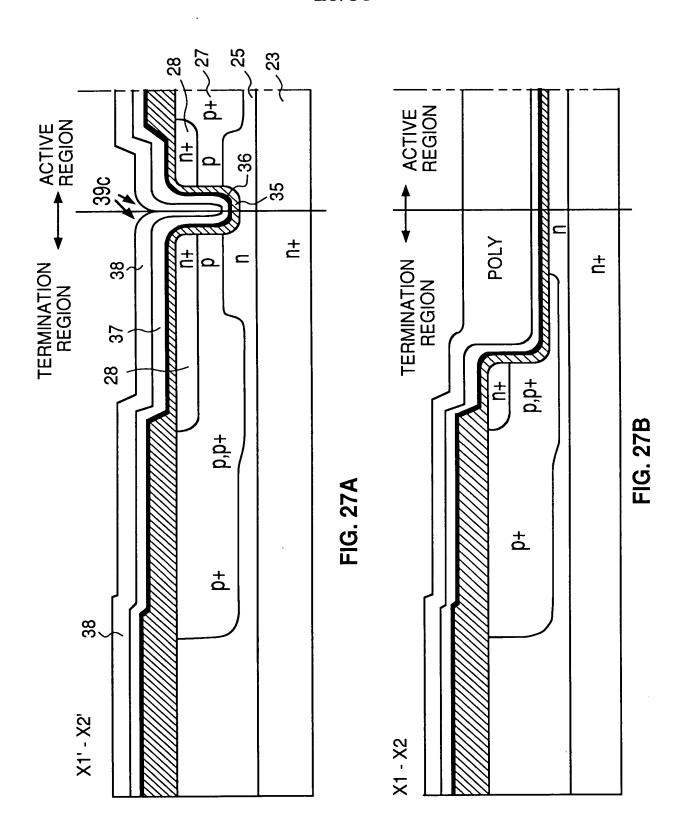




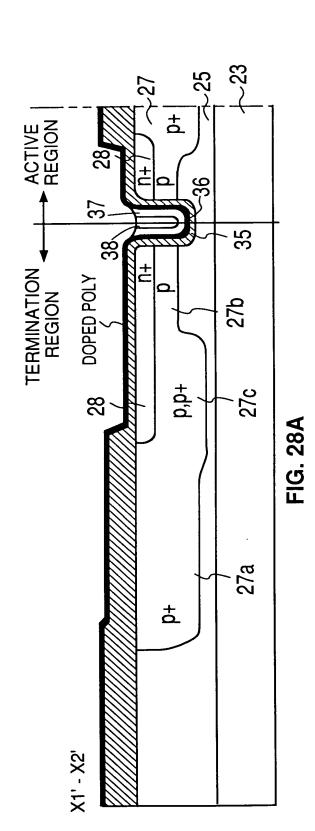
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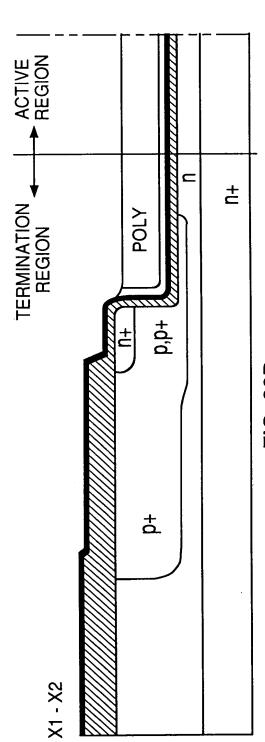


FIG. 28B

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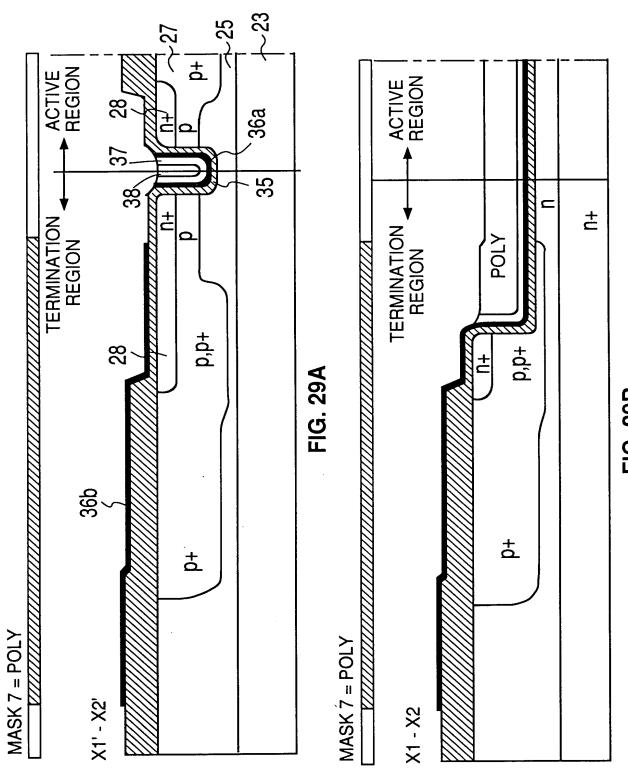


FIG. 29B



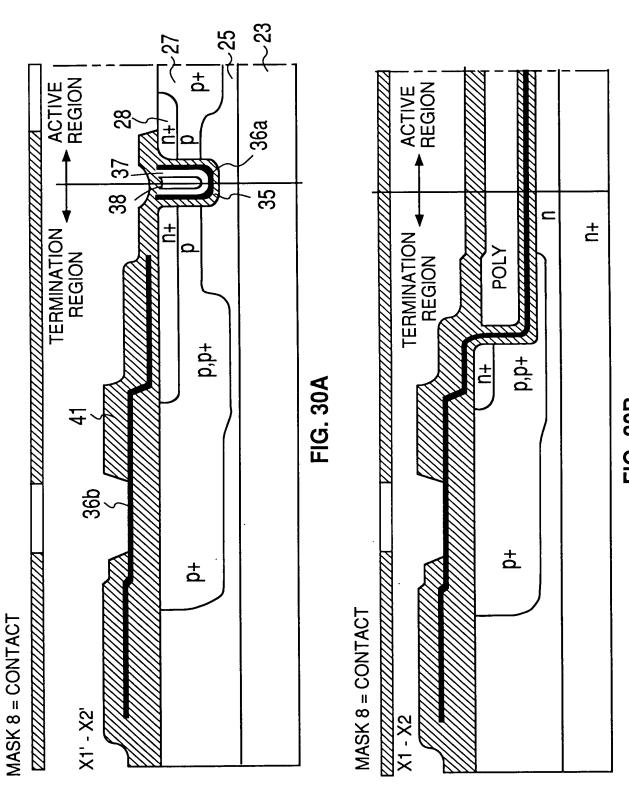
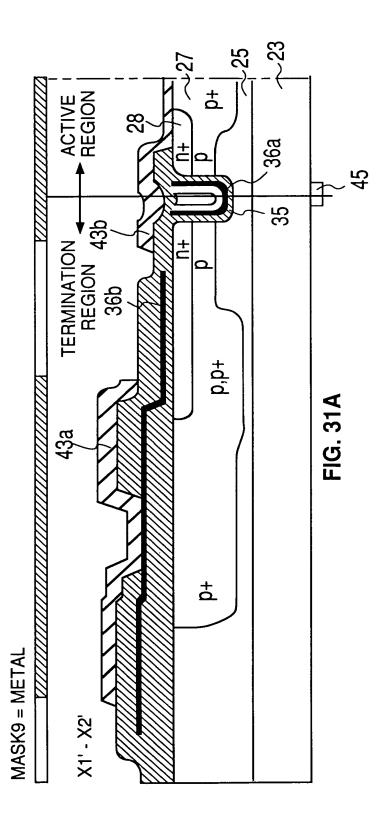


FIG. 30B

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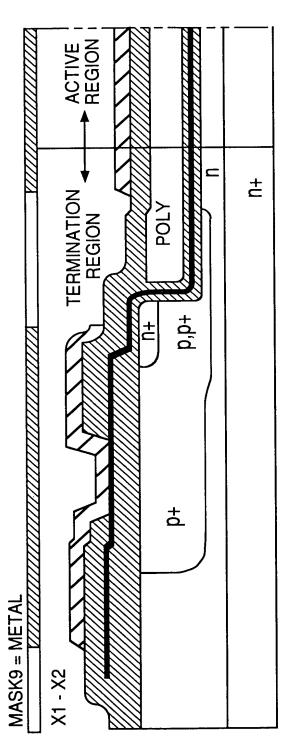


FIG. 31B



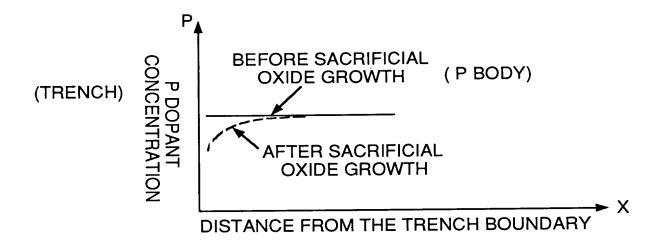


FIG. 32







DEVICE, RDSON SIMULATION - G32

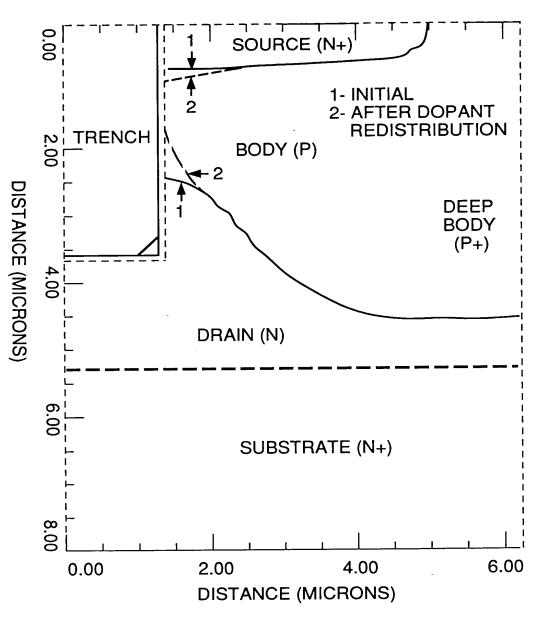


FIG. 33